

FCRM PTO-1449 (SUBSTITUTE)		Attorney Docket No.: GR 99 P 4724 US 09/677,545	Serial No.
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Applicant Martin Schrems et al.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))		Filing Date October 2, 2000	Group Art Unit

## U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
Cr	A	4,937,205	06/26/90	Nakayama et al.			
Cr	B	5,189,503	02/23/93	Suguro et al.			
Cr	C	5,250,829	10/05/93	Bronner et al.			
Cr	D	5,344,381	09/06/94	Cabrera y Lopez Caram			
	E						
	F						
	G						
	H						
	I						

## FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
	J						
	K						
	L						
	M						
	N						

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

Cr	O	Frank S. Becker et al.: "Low Pressure Deposition of Doped SiO <sub>2</sub> by Pyrolysis of Tetraethylorthosilicate (TEOS)", Journal of the Electrochemical Society, Vol. 136, No. 10, October 1989, pp. 3033-3043;
Cr	P	C.N. Ransom et al.: "Shallow n <sup>+</sup> Junctions in Silicon by Arsenic Gas-Phase Doping", Journal of the Electrochemical Society, Vol. 141, No. 5, May 1994, pp. 1378-1381

EXAMINER	DATE CONSIDERED
Cr	6-19-02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609;  
Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.